7-10-01

S/N Unknown PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Wendell P. Noble et al.	Examiner: Unknown	
Serial No.:	Unknown	Group Art Unit: Unknown	
Filed:	Herewith	Docket: 303.330US3	
Title:	ULTRA HIGH DENSITY FLASH MEMORY		

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
Washington, D.C. 20231

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for review in connection with the above-identified patent application. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner be returned to the Applicants.

In accordance with 37 C.F.R. §1.98(d), copies of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicants' prior U.S. application, Serial No. 09/035,304, filed on February 27, 1998, which is relied upon for an earlier filing date under 35 U.S.C. §120.

Applicants respectfully request consideration of these references during prosecution of the above-identified matter. The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

WENDELL P. NOBLE ET AL.

By their Representatives,

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Date 5/29/2001 By Edward J. Brooks

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"Express Mail" mailing label number: EL671639402US
Date of Deposit: May 29, 2001
This paper or fee is being deposited on the date indicated above with the United States Postal Service pursuant to 37 CFR 1.10, and is addressed to the Commissioner for Patents, Box Patent Application, Washington, D.C. 20231.

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*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449*	Atty. Docket No.: 303.330US3	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Wendell P. Noble et al.	
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